

CLAIMS

1. A method of production of a silicon carbide single crystal by precipitation from a solution using a temperature gradient furnace giving a temperature  
5 gradient to a columnar workpiece in its longitudinal direction, comprising:

using as said temperature gradient furnace a temperature gradient furnace provided with heat insulating walls surrounding an outer circumference of  
10 said columnar workpiece, a heating unit for heating a bottom end of said columnar workpiece through a heating susceptor, and a cooling unit for cooling a top end of said columnar workpiece through a cooling susceptor;

stacking, inside said furnace in order  
15 from the bottom, a source material rod comprised of silicon carbide, a solvent, a seed crystal, and a support rod supporting said seed crystal at its bottom end so as to form said columnar workpiece, heating a bottom end of said source material rod as said bottom end of the  
20 columnar workpiece by said heating unit, and cooling a top end of said support rod as said top end of the columnar workpiece by said cooling unit so as to form a temperature gradient inside said columnar workpiece so that the top end face becomes lower in temperature than  
25 the bottom end face of said solvent; and

causing a silicon carbide single crystal to grow continuously to the bottom starting from said seed crystal, wherein said method further comprises:

using an inside cylindrical susceptor  
30 tightly surrounding the outer circumference of said columnar workpiece.

2. A method of production of a silicon carbide single crystal as set forth in claim 1, further  
35 comprising carrying said inner cylindrical susceptor at its bottom end on the top end of said source material rod and suspending said support rod by a ring-shaped member screwed over its top outer circumference from the top end

of said inner cylindrical susceptor so as to hold it in a manner adjustable in vertical position.

3. A method of production of a silicon carbide single crystal as set forth in claim 1 or 2, further comprising using as said source material rod a source material rod provided with one of a cylindrical or spherical counter bore at its top face.

4. A method of production of a silicon carbide single crystal as set forth in any one of claims 1 to 3, further comprising using as said solvent one comprised of Si and at least one type of coexisting element selected from Y, Sc, a lanthanoid, an element of Group I of the Periodic Table, and an element of Group II of the Periodic Table.

5. A method of production of a silicon carbide single crystal by precipitation from a solution using a temperature gradient furnace giving a temperature gradient to a columnar workpiece in its longitudinal direction, comprising:

using as said temperature gradient furnace a temperature gradient furnace provided with heat insulating walls surrounding an outer circumference of said columnar workpiece, a heating unit for heating a bottom end of said columnar workpiece through a heating susceptor, and a cooling unit for cooling a top end of said columnar workpiece through a cooling susceptor;

stacking, inside said furnace in order from the bottom, a source material rod comprised of silicon carbide, a solvent, a seed crystal, and a support rod supporting said seed crystal at its bottom end so as to form said columnar workpiece, heating a bottom end of said source material rod as said bottom end of the columnar workpiece by said heating unit, and cooling a top end of said support rod as said top end of the columnar workpiece by said cooling unit so as to form a temperature gradient inside said columnar workpiece so that the top end face becomes lower in temperature than

the bottom end face of said solvent; and  
causing a silicon carbide single crystal  
to grow continuously to the bottom starting from said  
seed crystal, wherein said method further comprises:

5                    using as said source material rod a source  
material rod provided with a counter bore of an inside  
diameter equal to an outside diameter of said seed  
crystal on the top face and pulling said support rod at  
the time where a predetermined thickness of the single  
10 crystal is grown so as to remove said single crystal from  
said solvent.

6. A method of production of a silicon carbide  
single crystal as set forth in claim 5, further  
comprising surrounding said columnar workpiece with an  
15 heat insulating cylinder interposed between said heat  
insulating walls and said columnar workpiece, making a  
bottom end part of said support rod to have a shape with  
an outside diameter larger than other parts of said  
columnar workpiece, and bringing an outer circumferential  
20 face of the bottom end part of said support rod into  
contact with an inner circumferential face of said heat  
insulating cylinder.

7. A method of production of a silicon carbide  
single crystal as set forth in claim 5 or 6, further  
25 comprising using a top end holder of said support rod  
provided with a buffer mechanism allowing free rise of  
said support rod.